SGB2433Z

DC to 4GHZ ACTIVE BIAS GAIN BLOCK

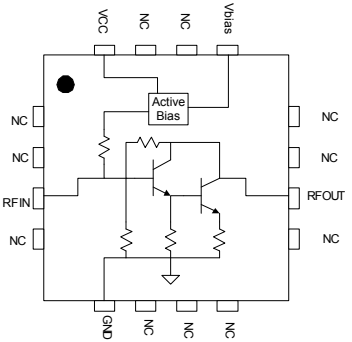
RFMD Green, RoHS Compliant, Pb-Free (Z Part Number)
Package: 3x3 QFN, 16-Pin

Product Description

RFMD's SGB2433Zis a high performance SiGe HBT MMIC amplifier utilizing a Darlington configuration with an active bias network. The active bias network provides stable current over temperature and process Beta variations. Designed to run directly from a 3Vto5V supply the SGB2433Z does not require a drop resistor as compared to typical Darlington amplifiers. This robust amplifier features a Class 1C ESD rating, low thermal resistance, and unconditional stability. The SGB2433Z product is designed for high linearity 3V gain block applications that require small size and minimal external components. It is on chip matched to 50Ω and an external bias inductor choke is required for the application band.

Optimum Technology Matching® Applied

- ☐ GaAs HBT
- ☐ GaAs MESFET
- ☐ InGaP HBT
- ☐ SiGe BiCMOS
- ☐ Si BiCMOS
- ☑ SiGe HBT
- ☐ GaAs pHEMT
- ☐ Si CMOS
- ☐ Si BJT
- ☐ GaN HEMT
- ☐ RF MEMS



Features

- High Reliability SiGe HBT Technology
- Robust Class 1C ESD
- Simple and Small Size
- P_{1dB}=6.9dBm at 1950MHz
- IP_3=18.0dBm at 1950MHz
- Low Thermal Resistance=221C/W

Applications

- 3V Battery Operated Applications
- LO Buffer Amp
- RF Pre-Driver and RF Receive Path

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Small Signal Gain		19.1		dB	850MHz
	15.7	17.2	18.7	dB	1950MHz
		16.2		dB	2400MHz
Output Power at 1dB Compression		7.7		dBm	850MHz
	5.4	6.9		dBm	1950MHz
		6.2		dBm	2400MHz
Output Third Order Intercept Point		19.5		dB	850MHz
	16.0	18.0		dB	1950MHz
		18.0		dB	2400MHz
Noise Figure		3.5	4.5	dB	1950MHz
Frequency of Operation	DC		4000	MHz	
Current, I_C	21.0	25.0	29.0	mA	
Input Return Loss	10.0	13.4		dB	1950MHz
Output Return Loss	10.0	13.6		dB	1950MHz
Thermal Resistance		221		°C/W	junction to backside

Test Conditions: Z_O=50Ω, V_{CC}=3V, I_C=25mA, T=30°C

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Absolute Maximum Ratings

Parameter	Rating	Unit
Current (I_C total)	60	mA
Max Device Voltage (V_D)	5	V
Max RF Input Power	20	dBm
Power Dissipation	0.2	W
Max Junction Temperature (T_J)	150	°C
Operating Temperature Range *(T_L)	-55 to +105	°C
Max Storage Temperature	-40to+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one.
Bias Conditions should also satisfy the following expression:
$I_D V_D < (T_J - T_L)/R_{TH, j\text{-}l}$

Caution! ESD sensitive device.

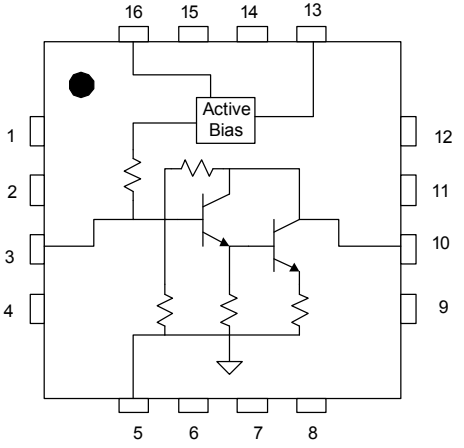
Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EUDirective2002/95/EC (at time of this document revision).

Detailed Performance Table: V_{CC}=3V, I_C=25mA, T=25°C, Z=50Ω

Parameter	Unit	100 MHz	500 MHz	850 MHz	1950 MHz	2400 MHz	3500 MHz
Small Signal Gain (G)	dB	19.7	19.5	19.1	17.2	16.2	14.0
Output 3rd Order Intercept Point (OIP_3)	dBm		20.0	19.5	18.0	18.0	
Output Power at 1dB Compression (P_{1dB})	dBm		8.3	7.7	6.9	6.2	
Input Return Loss (IRL)	dB	25.0	19.9	17.1	13.4	12.7	10.5
Output Return Loss (ORL)	dB	20.5	18.9	17.1	13.6	13.1	13.0
Reverse Isolation (S_{12})	dB	22.4	22.6	22.9	23.7	23.9	24.5
Noise Figure (NF)	dB	3.8	3.2	3.2	3.5	3.9	4.3

Simplified Device Schematic



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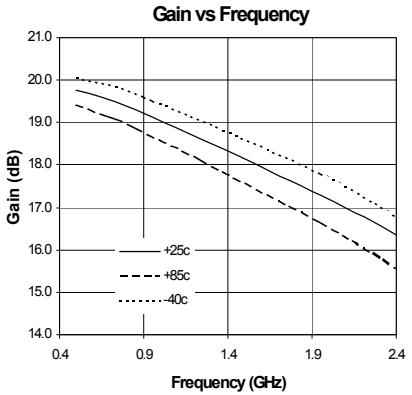
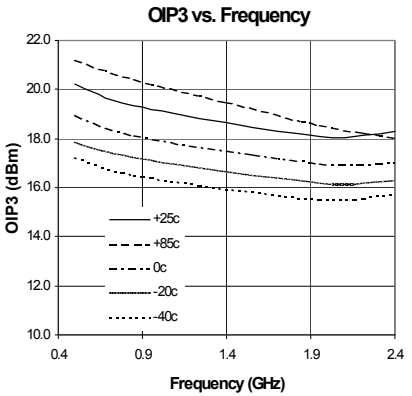
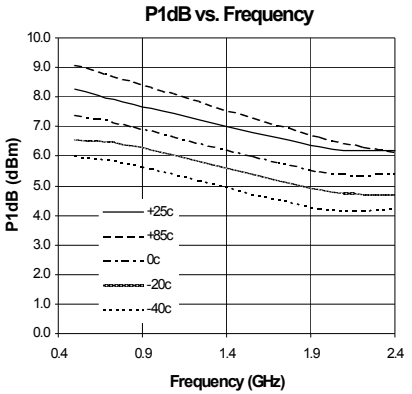
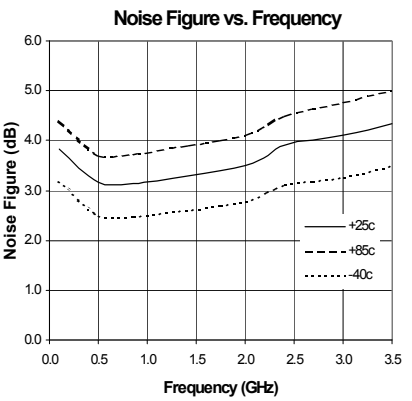
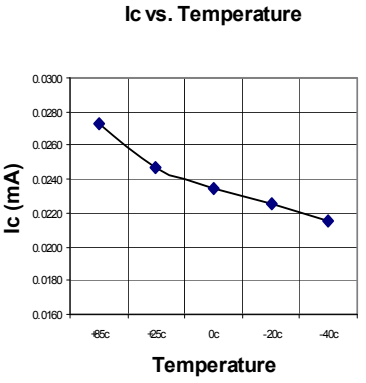
Evaluation Board Data (V_{CC}=V_{BIAS}=3.0V, I_C=25mA) Bias Tee substituted for DC feed inductor (L1)

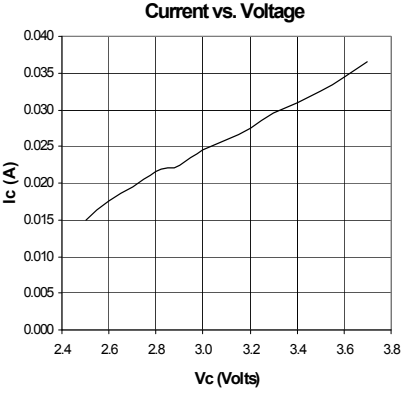




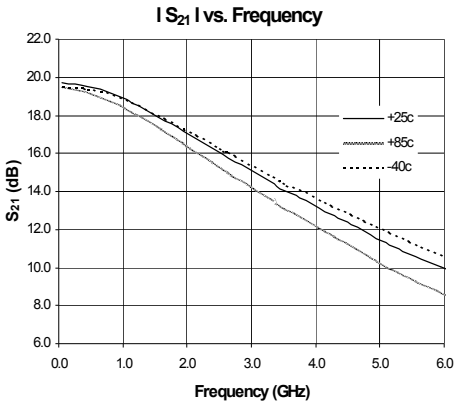


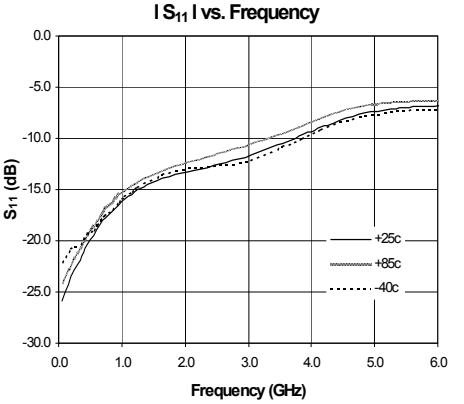


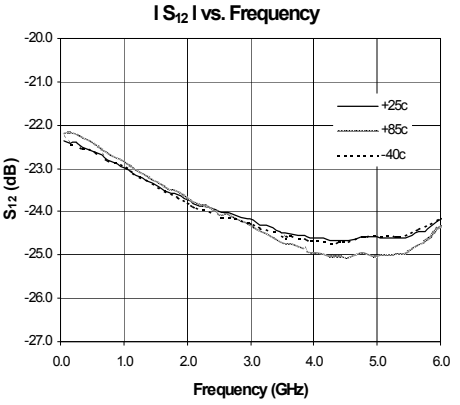


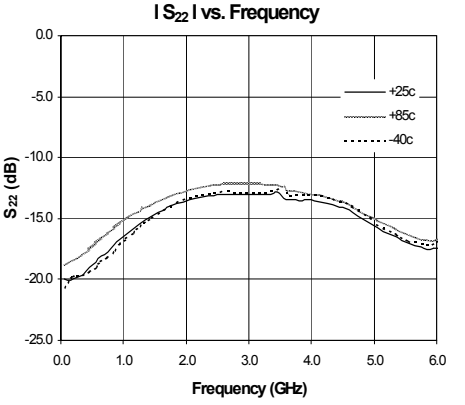


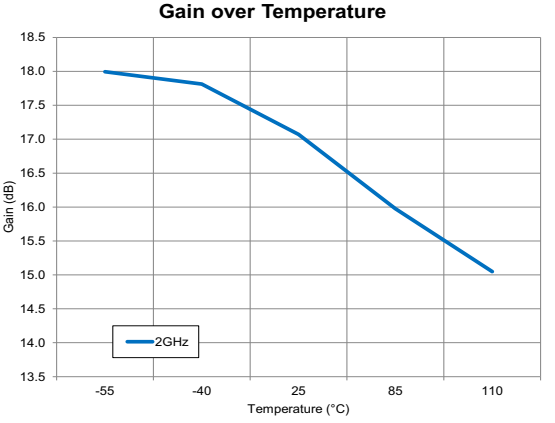
Evaluation Board Data (V_{CC}=V_{BIAS}=3.0V, I_C=25mA) Bias Tee substituted for DC feed inductor (L1) cont.











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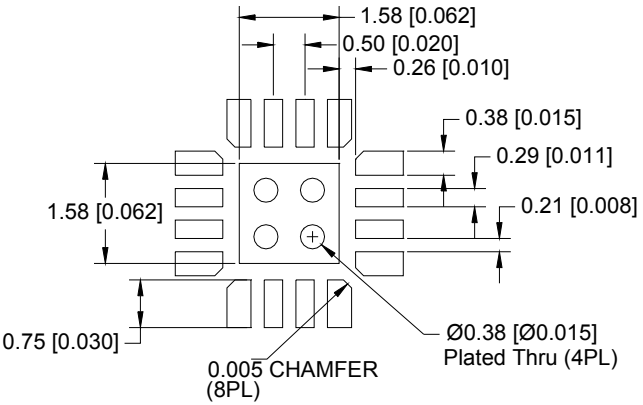
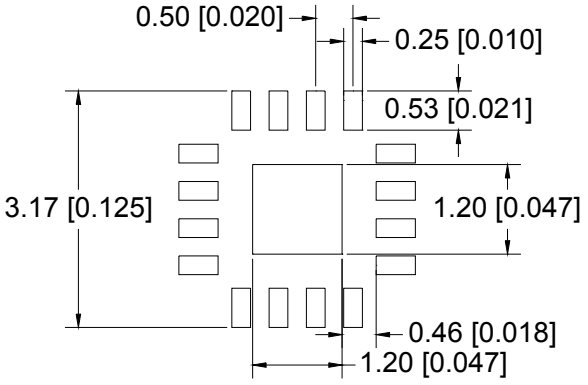
Recommended Land Pattern

Dimensions in millimeters (inches)



Recommended PCB Soldermask for Land Pattern



Package Drawing

Dimensions in millimeters (inches)

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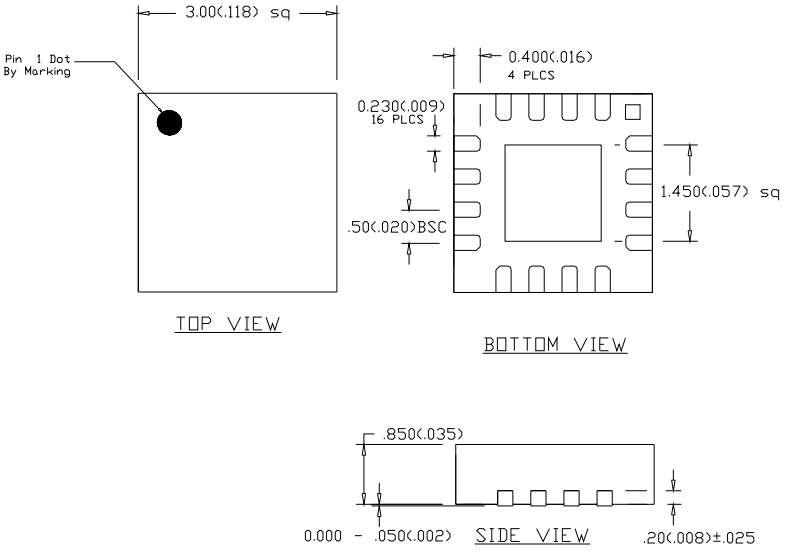
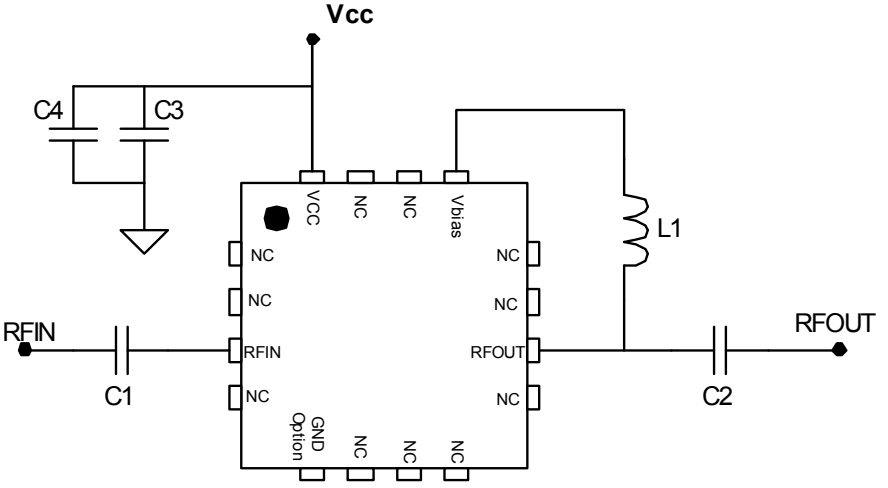
Refer to drawing posted at www.rfmd.com for tolerances.



Typical Evaluation Board Schematic for 3.0V



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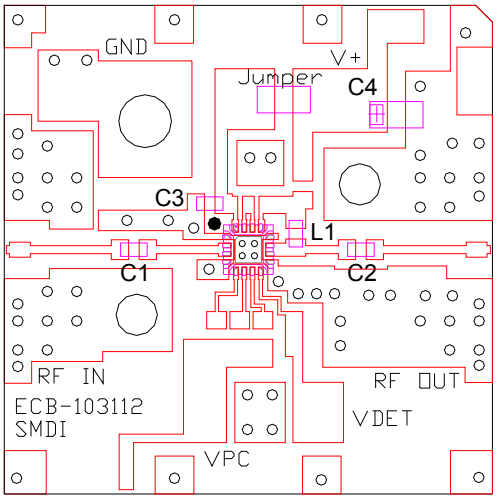
Evaluation Board Layout and Bill of Materials



Board material GETEK, 31mil thick, Dk=4.2, 1oz copper.

Component Values By Band

Designator	500MHz	850MHz	1950MHz	2400MHz
C3	1000pF	1000pF	1000pF	1000pF
C4*	1uF	1uF	1uF	1uF
C1, C2	220pF	68pF	43pF	22pF
L1	68nH	33nH	22nH	18nH

*C4 is optional depending on application and filtering. Not required for SGB device operation.

Note: The amplifier can be run from a 5V supply by simply inserting a 82Ω resistor in series with V_{CC}.

Ordering Information

Part Number	Reel Size	Devices/Reel
SGB2433Z	13"	3000

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